

STPOWER™ Transistors in the 10 years longevity program



ST's 10-year longevity commitment program ensures continuity and stability of supply for ST's customers

STMicroelectronics has selected certain STPOWER Transistors to take part in the 10 years longevity commitment program. ST's Product Longevity Commitment Program helps customer protect their design investments by ensuring a minimum availability of 10 years on selected devices starting from the notification date. For more information about ST's 10-year longevity commitment program, visit www.st.com/longevity



ST'S LONGEVITY COMMITMENT PROGRAM

- High performance and high quality even in harsh industrial environments
- 10 years longevity from product introduction date
 - The 10-year longevity commitment includes the period of notification as set forth in the standard STMicroelectronics end-of-life notification policy.
 - In case of significant volume decrease, technology or manufacturing changes, a switch to a comparable product, could be decided by STMicroelectronics who will notify customers using the product/process change policy (PCN).

LIST OF LONGEVITY PRODUCTS

STPOWER MOSFETs

ST's **power MOSFET** portfolio offers a broad range of breakdown voltages from 350 to 1700 V, with low gate charge and low on-resistance, combined with state-of-the-art packaging. ST's process technology ensures an enhanced power handling capability, resulting in high-efficiency solutions.

- N-channel STPOWER MOSFETs, above 700 V:
STD2N80K5, STD8N80K5, STF10N80K5, STF10N95K5, STF13N80K5, STF14N80K5, STF25N80K5, STF7N80K5, STF8N80K5, STH12N120K5-2, STP12N120K5, STP15N95K5, STH3N150-2, from March 25th 2019
- N-channel STPOWER MOSFETs, 350 to 700 V:
STD10N60M2, STD13N60M2, STD16N50M2, STD5N60M2, STF13N60M2, STF16N65M2, STF18N60M2, STF28N60M2, STF40N60M2, STP18N60M2, STW28N60M2, STW33N60M2, STW40N60M2, STW48N60M2, STW70N60M2, STF24N60DM2, STP24N60DM2, STW33N60DM2, STW43N60DM2, STW48N60DM2, STW70N60DM2, STW78N65M5, from March 25th 2019

STPOWER IGBTs

ST offers a comprehensive portfolio of **IGBTs** (Insulated Gate Bipolar Transistors) ranging from 300 to 1250 V, both in planar punch-through (PT) and trench-gate field-stop (TFS) technologies. Offering an optimal trade-off between switching performance and on-state behavior ST's IGBTs are suitable for **industrial** and **automotive** segments

- STPOWER IGBTs, 600 to 650 V:
STGD5H60DF, STGW40V60DF, STGW60V60DF, STGW40H65DFB, STGW60H65DFB, STGW80H65DFB, STGWA60H65DFB, STGWT60H65DFB, from March 25th 2019
- STPOWER IGBT, 1200 V:
STGWA40H120DF2, from March 25, 2019.

STPOWER Modules

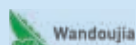
ST's power module portfolio includes both our **SLLIMM™** families of Intelligent Power Modules (IPM) as well as **ACEPACK™** Power Modules for all types of power switching applications.

Our wide **STPOWER** product portfolio combined with state-of-the-art packaging and protections for high reliability and safety helps designers find the right solutions for customized, high-efficiency applications that will last a long lifetime.

- STPOWER SLLIMM™ IPM:
STGIB10CH60TS-L, from March 25, 2019.

To explore the complete STPOWER™ product portfolio, visit www.st.com or use our [ST-MOSFET-Finder](#) and [ST-IGBT-Finder](#) mobile app for Android and iOS

ST-MOSFET-Finder mobile app



ST-IGBT-Finder mobile app

